and adapted to carry a semiconductor wafer 135 and bring it in contact with the pad 140 for polishing. Although FIG. 1 shows the wafer carrier 130 located directly over the pad 140, the wafer carrier 130 may be located with only a portion of the carrier 130 over the pad 140 in order to enhance the application of the present invention. FIG. 2 shows the wafer carrier 130 (along with wafer 135) misaligned over and with respect to the center of the pad 140. The wafer carrier is further arranged to rotate, such as shown by directional arrow 131. Conditioning wheel 110 is arranged over the pad 140 and used to condition the pad, responsive to detecting center-offset polishing. Supply 120 is used to supply conditioning materials such as water or de-ionized water to the pad 140.

On pages 9-10, lines 16-21 and 1-2 respectively:

For example, FIG. 2 shows a pad 140 that has been thinned near the edge 230. The thickness at the center of the pad is greater than the thickness near the edge 230 of the pad 140. When a wafer 135 is held against the pad 140 having the edge 230 thinned, the center of the wafer 135 can be held at a location of the pad 140 having greater thickness than the edge 230. Due to the greater thickness near the center, the wafer 135 is polished center-fast. Alternatively, the center of the pad 140 could be thinned resulting in the edge having a greater thickness relative to the center thickness prior to thinning and enhancing center-slow polishing. In another alternative, various portions of the pad 140 could be thinned.